Unit: mm

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT8G133

Strobe Flash Applications

- Compact and Thin (TSSOP-8) package
- Enhancement-mode
- 4-V gate drive voltage: $V_{GE} = 4.0 \text{ V (min)}$ (@IC = 150 A)
- Peak collector current: IC = 150 A (max)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage	V _{CES}	400	V		
Gate-emitter voltage	DC	V_{GES}	± 6		
	Pulse	V _{GES}	± 8		
Collector current	Pulse (Note 1)	I _{CP}	150	A	
Collector power dissipation (t=10 s)	(Note 2a)	P _C (1)	1,4	> w	
	(Note 2b)	P _C (2)	0.6	W	
Junction temperature	Tj	150	°C		
Storage temperature range	T _{stg}	-55~150	°C		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal resistance, junction to ambient (t = 10 s) (Note2a)	R _{th (j-a)} (1)	114	°C/W
Thermal resistance , junction to ambient (t = 10 s) (Note2b)	R _{th (j-a)} (2)	208	°C/W

Marking (Note 3) Part No. (or abbreviation code) 8G133 Lot No. A line indicates lead (Pb)-free package or lead (Pb)-free finish.

TSSOP 8

8

1.2.3 EMITTER

4

GATE

5.6.7.8 COLLECTOR

JEDEC

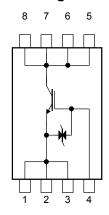
JEITA

TOSHIBA

2-3R1G

Weight: 0.035 g (typ.)

Circuit Configuration



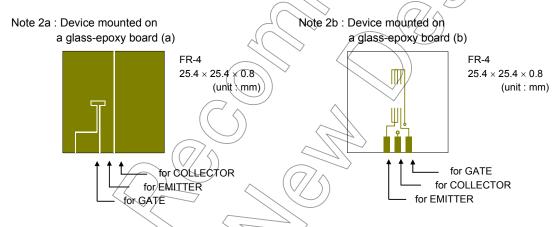
Note: For (Note 1), (Note 2a), (Note 2b) and (Note 3), Please refer to the next page.

Electrical Characteristics (Ta = 25°C)

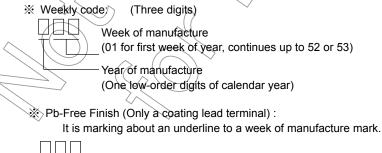
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GES}	$V_{GE} = \pm 6 \text{ V}, V_{CE} = 0$	_	_	± 10	μΑ
Collector cut-off of	current	I _{CES}	V _{CE} = 400 V, V _{GE} = 0	_	_	10	μΑ
Gate-emitter cut-	off voltage	V _{GE} (OFF)	$I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	0.7	1.05	1.4	V
Collector-emitter	saturation voltage	V _{CE (sat)}	I _C = 150 A, V _{GE} = 4 V		2.9	_	٧
Input capacitance)	C _{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	(F	2500		pF
Switching time	Rise time	t _r	$\begin{array}{c} 4 \text{ V} \\ 0 \\ \hline \\ V_{\text{IN}} : t_r \leq 100 \text{ ns} \\ t_f \leq 100 \text{ ns} \\ \hline \\ \text{Duty cycle} \leq 1\% \\ \end{array}$) 1	1.6		μ s
	Turn-on time	ton			1.7	_	
	Fall time	t _f			1.7	-	
	Turn-off time	t _{off}		- (2.0		

Note

Note 1: Please use devices on condition that the junction temperature is below 150°C Repetitive rating: pulse width limited by maximum junction temperature.

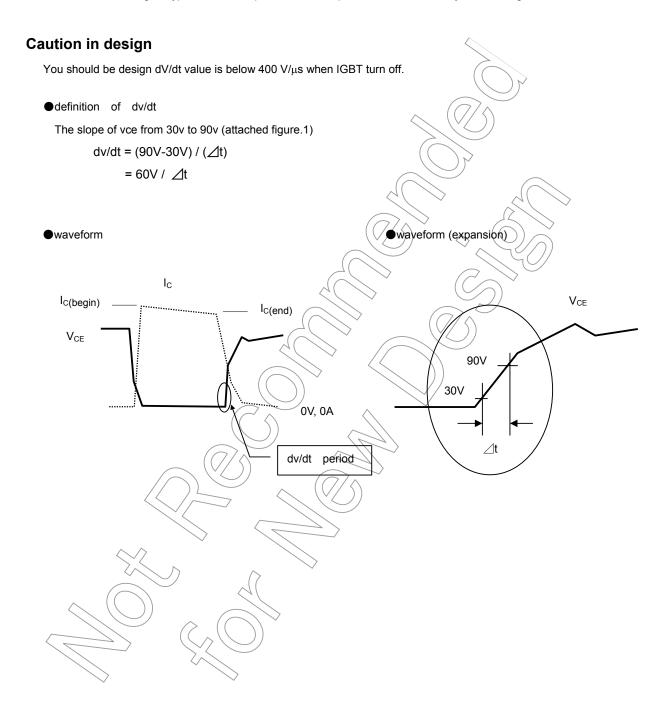


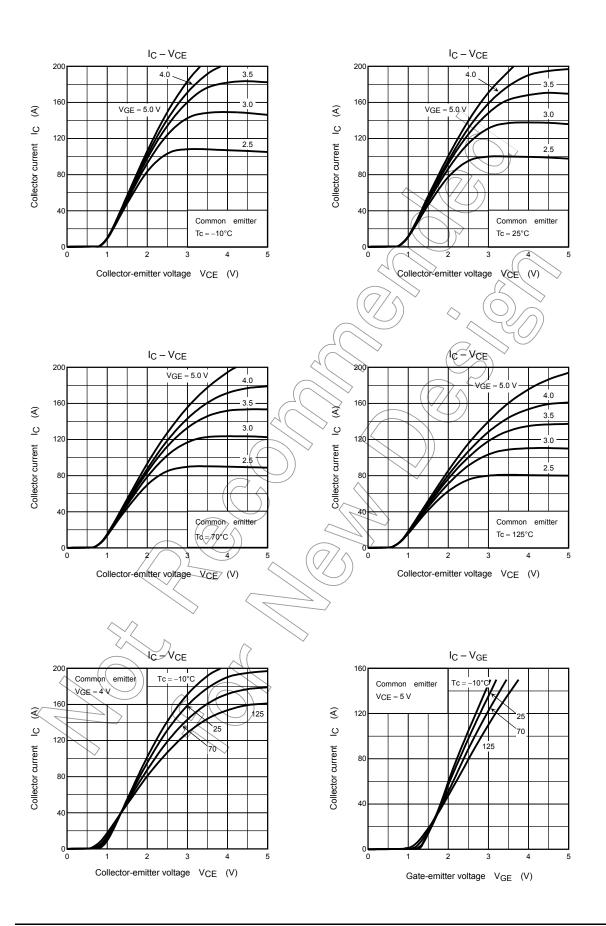
Note 3: O on lower right of the marking indicates Pin 1.

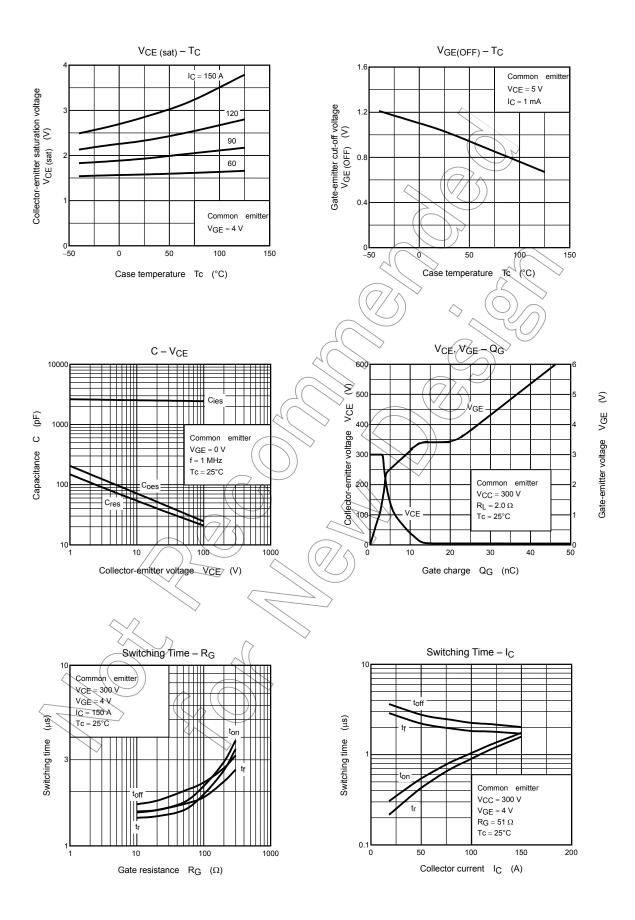


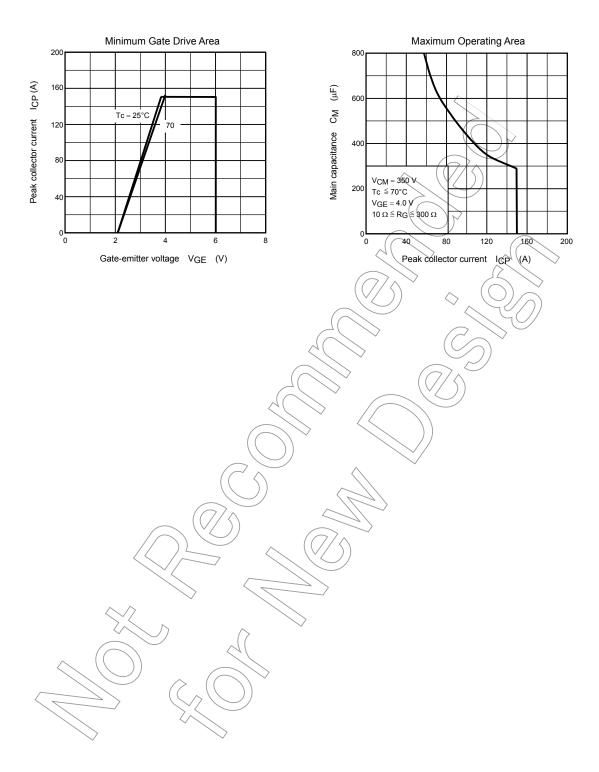
Caution on handling

This device is MOS gate type. Therefore , please care of a protection from ESD in your handling .











RESTRICTIONS ON PRODUCT USE

20070701-EN

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